



# PMV120ENEA

60 V, N-channel Trench MOSFET

4 March 2016

Product data sheet

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

## 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ }^\circ\text{C}$	-	-	60	V
$V_{GS}$	gate-source voltage		-20	-	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}$	[1]	-	2.1	A
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 2.1\text{ A}; T_j = 25\text{ }^\circ\text{C}$	-	96	123	m $\Omega$

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

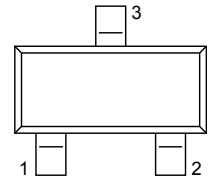
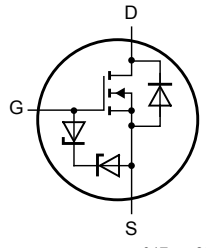


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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>TO-236AB (SOT23)</p>	 <p>017aaa255</p>
2	S	source		
3	D	drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV120ENEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

## 7. Marking

Table 4. Marking codes

Type number	Marking code
PMV120ENEA	DX% [1]

[1] % = placeholder for manufacturing site code

## 8. Limiting values

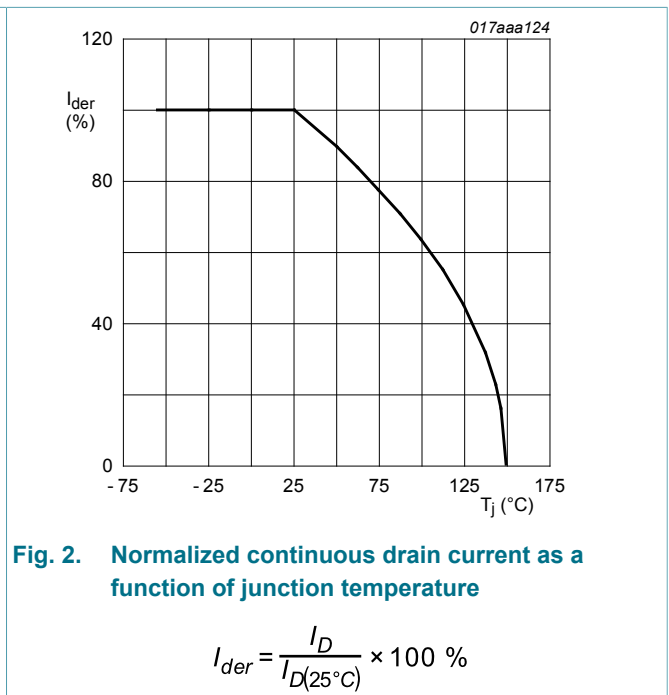
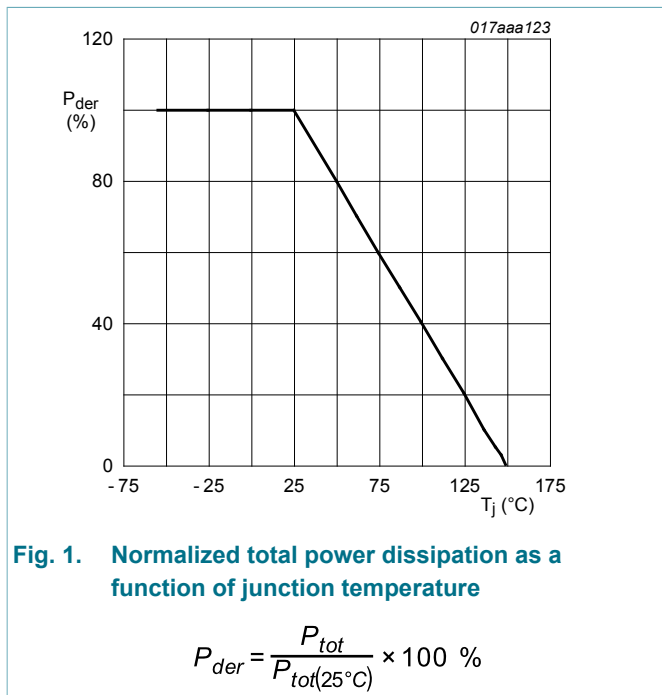
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j = 25\text{ }^\circ\text{C}$	-	60	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ }^\circ\text{C}$	[1]	2.1	A
		$V_{GS} = 10\text{ V}; T_{amb} = 100\text{ }^\circ\text{C}$	[1]	1.3	A
$I_{DM}$	peak drain current	$T_{amb} = 25\text{ }^\circ\text{C}; \text{single pulse}; t_p \leq 10\text{ }\mu\text{s}$	-	8.3	A
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$T_{j(\text{init})} = 25\text{ }^\circ\text{C}; I_D = 0.3\text{ A}; \text{DUT in avalanche (unclamped)}$	-	9	mJ
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ }^\circ\text{C}$	[2]	513	mW

Symbol	Parameter	Conditions		Min	Max	Unit
			[1]	-	1.05	W
		T <sub>sp</sub> = 25 °C		-	6.4	W
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
<b>Source-drain diode</b>						
I <sub>s</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.8	A
<b>ESD maximum rating</b>						
V <sub>ESD</sub>	electrostatic discharge voltage	HBM	[3]	-	2000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [3] Measured between all pins.



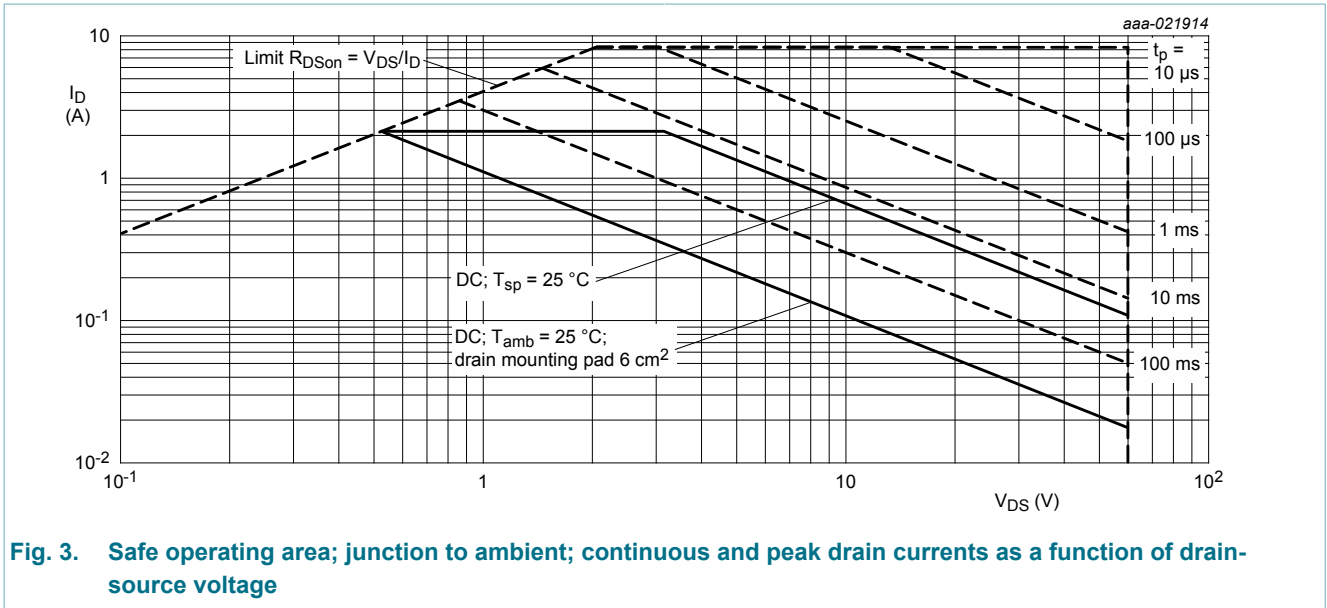


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	212	244	K/W
			[2]	-	104	119	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	17	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

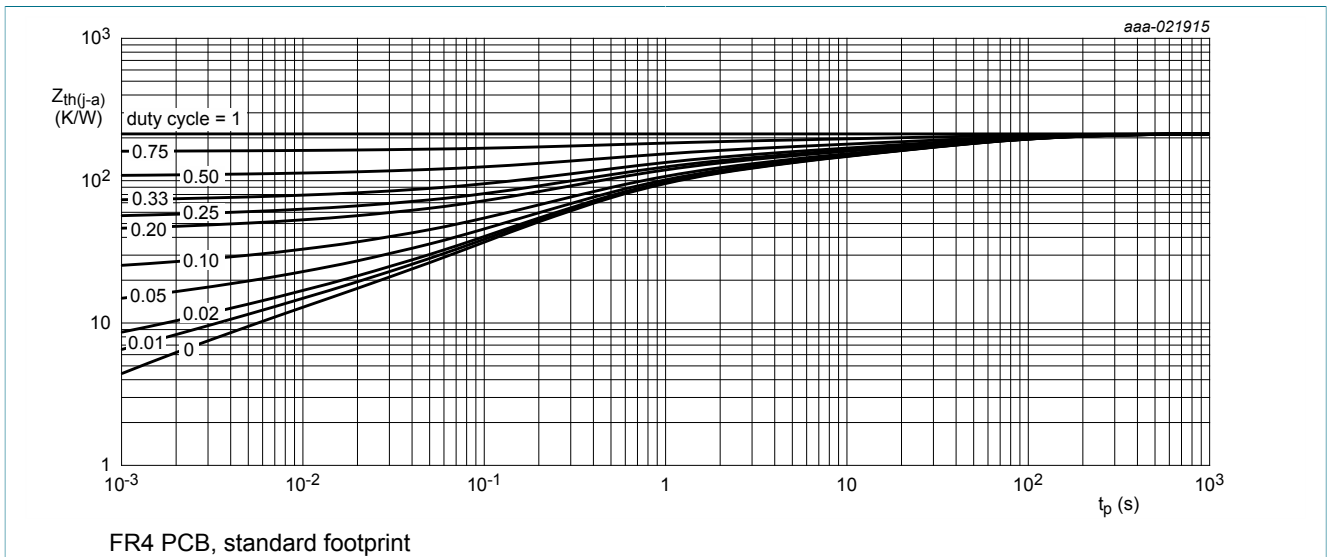


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

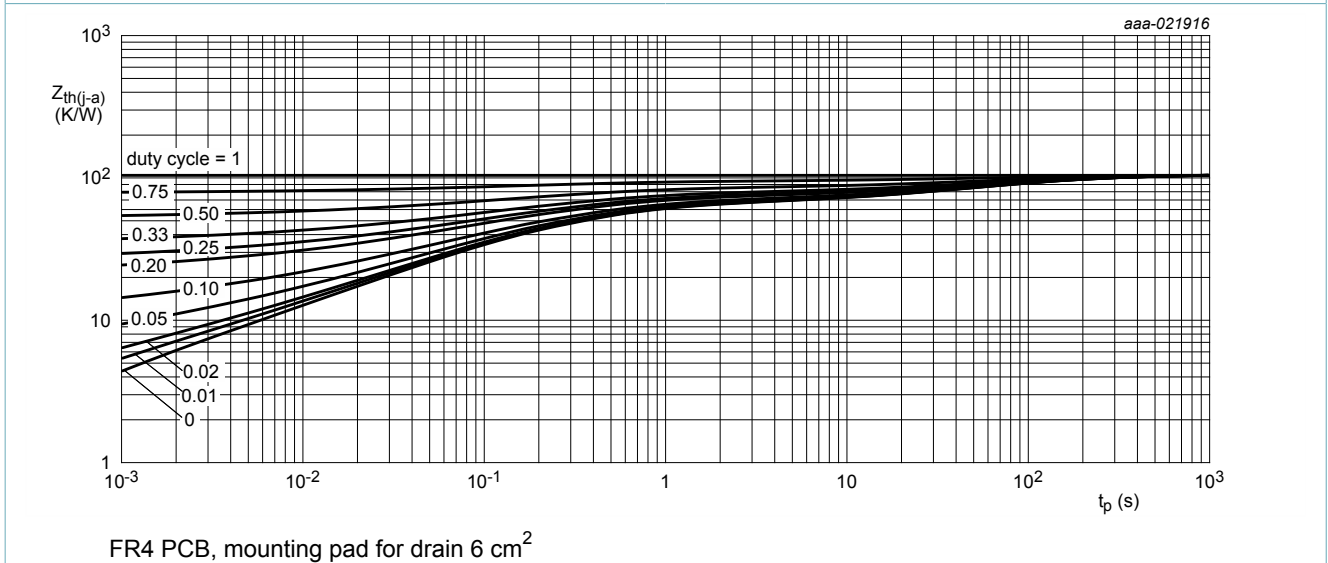


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	1.3	1.7	2.7	V
$I_{DSS}$	drain leakage current	$V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	10	$\mu A$
		$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-10	$\mu A$
		$V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	$\mu A$
		$V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-1	$\mu A$
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 V; I_D = 2.1 A; T_j = 25 \text{ }^\circ C$	-	96	123	m $\Omega$
		$V_{GS} = 10 V; I_D = 2.1 A; T_j = 150 \text{ }^\circ C$	-	192	246	m $\Omega$
		$V_{GS} = 4.5 V; I_D = 1.9 A; T_j = 25 \text{ }^\circ C$	-	108	146	m $\Omega$
$g_{fs}$	forward transconductance	$V_{DS} = 10 V; I_D = 0.9 A; T_j = 25 \text{ }^\circ C$	-	10.2	-	S
$R_G$	gate resistance	$f = 1 \text{ MHz}$	-	10	-	$\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 30 V; I_D = 2.1 A; V_{GS} = 10 V; T_j = 25 \text{ }^\circ C$	-	5.9	7.4	nC
$Q_{GS}$	gate-source charge		-	0.6	-	nC
$Q_{GD}$	gate-drain charge		-	1.1	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 30 V; f = 1 \text{ MHz}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	275	-	pF
$C_{oss}$	output capacitance		-	24	-	pF
$C_{riss}$	reverse transfer capacitance		-	17	-	pF
$t_{d(on)}$	turn-on delay time		$V_{DS} = 30 V; I_D = 2.1 A; V_{GS} = 10 V; R_{G(ext)} = 6 \Omega; T_j = 25 \text{ }^\circ C$	-	6.4	-
$t_r$	rise time	-		8.9	-	ns
$t_{d(off)}$	turn-off delay time	-		15.9	-	ns
$t_f$	fall time	-		6.3	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 0.8 A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.8	1.2	V

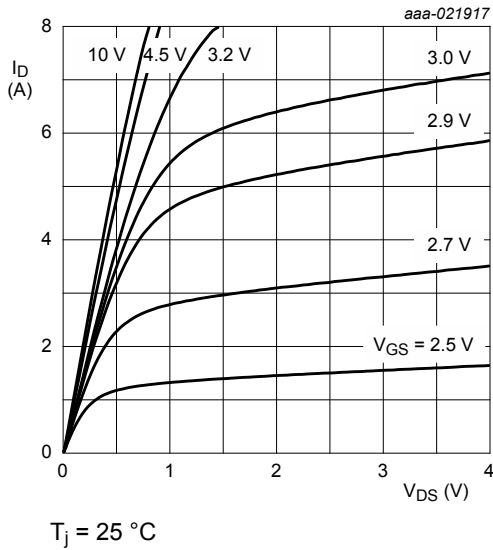


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

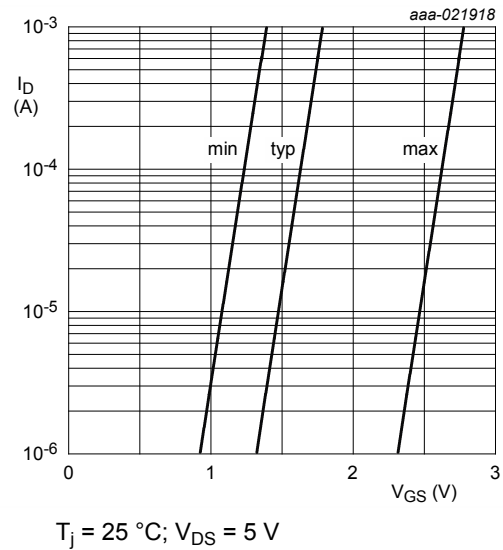


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

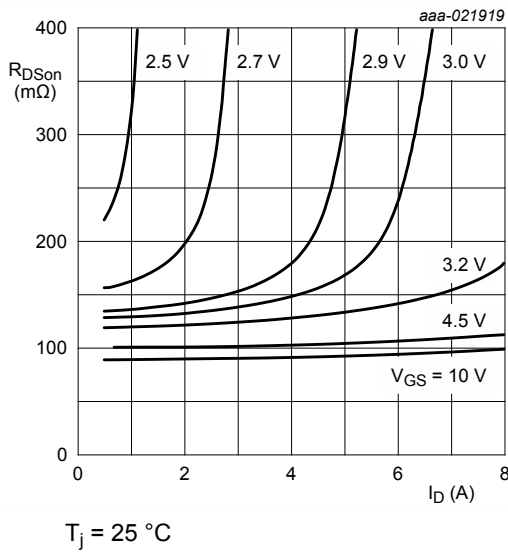


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

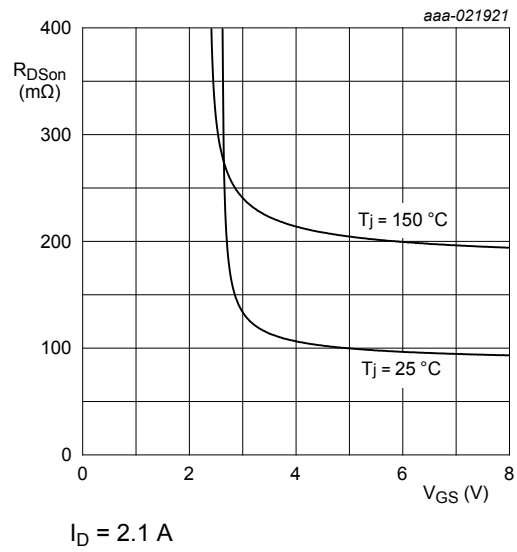
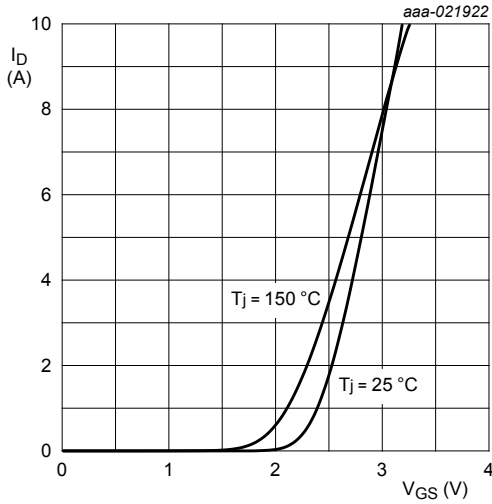
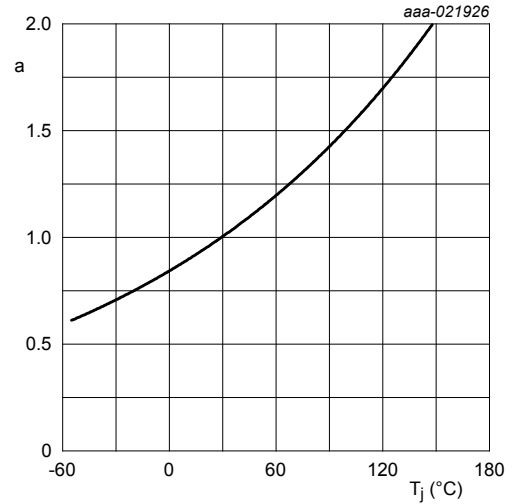


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



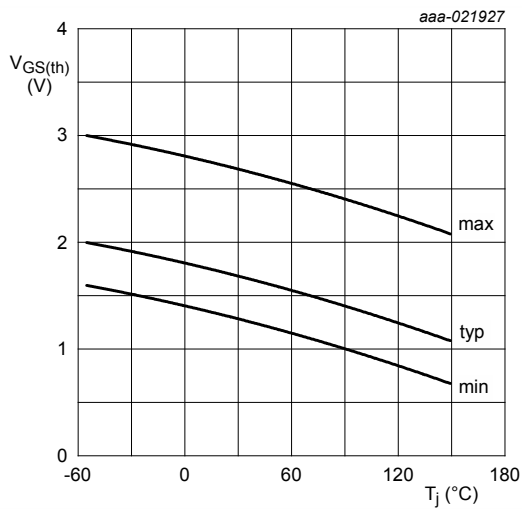
$$V_{DS} > I_D \times R_{DSon}$$

**Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



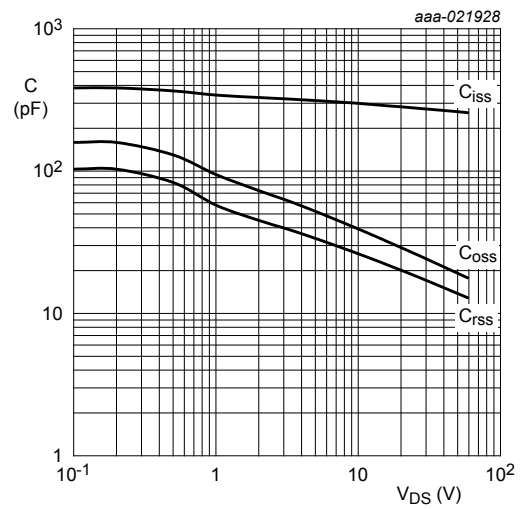
**Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values**

$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$



$$I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$$

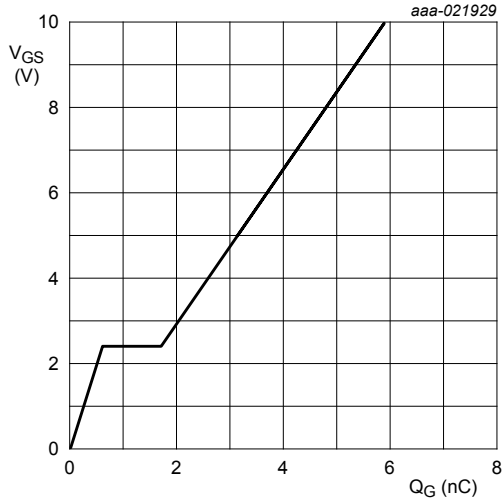
**Fig. 12. Gate-source threshold voltage as a function of junction temperature**



$$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$$

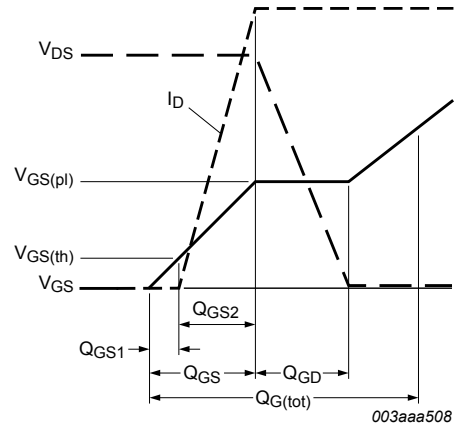
**Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



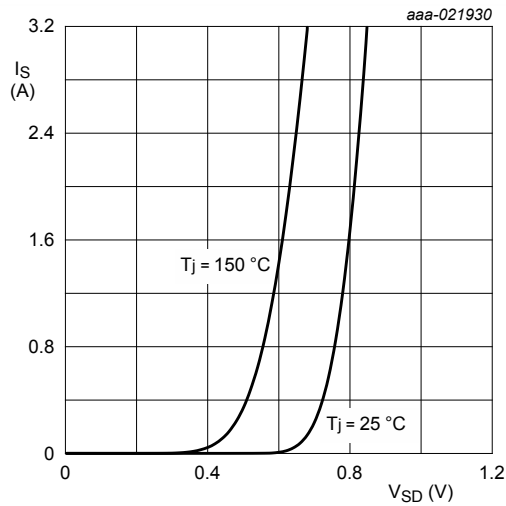


$I_D = 2.1 \text{ A}; V_{DS} = 30 \text{ V}; T_{amb} = 25 \text{ }^\circ\text{C}$

**Fig. 14. Gate-source voltage as a function of gate charge; typical values**



**Fig. 15. MOSFET transistor: Gate charge waveform definitions**



$V_{GS} = 0 \text{ V}$

**Fig. 16. Source current as a function of source-drain voltage; typical values**

## 11. Test information

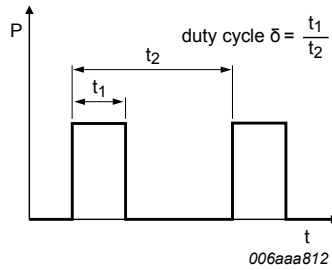


Fig. 17. Duty cycle definition

### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline

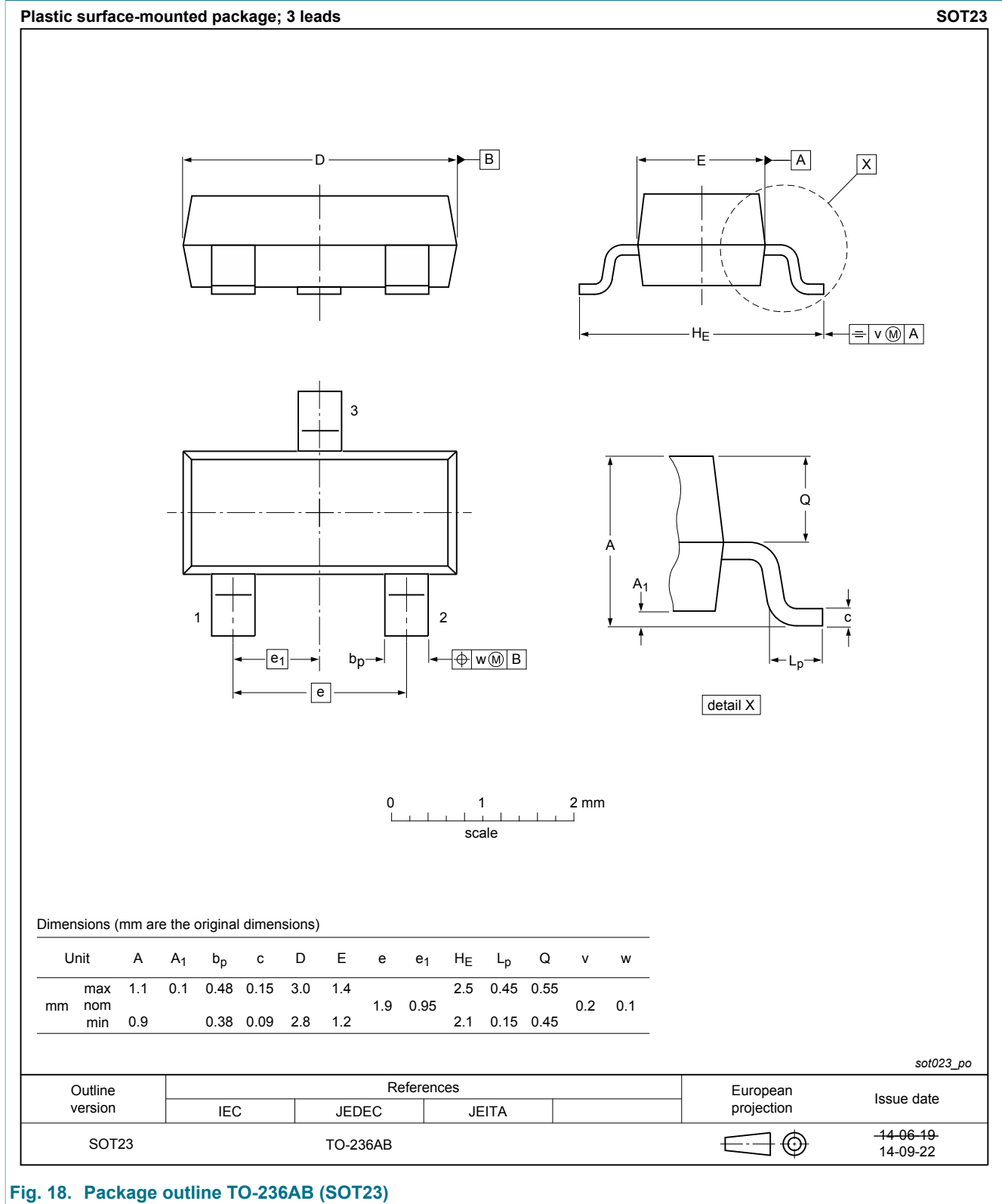


Fig. 18. Package outline TO-236AB (SOT23)

### 13. Soldering

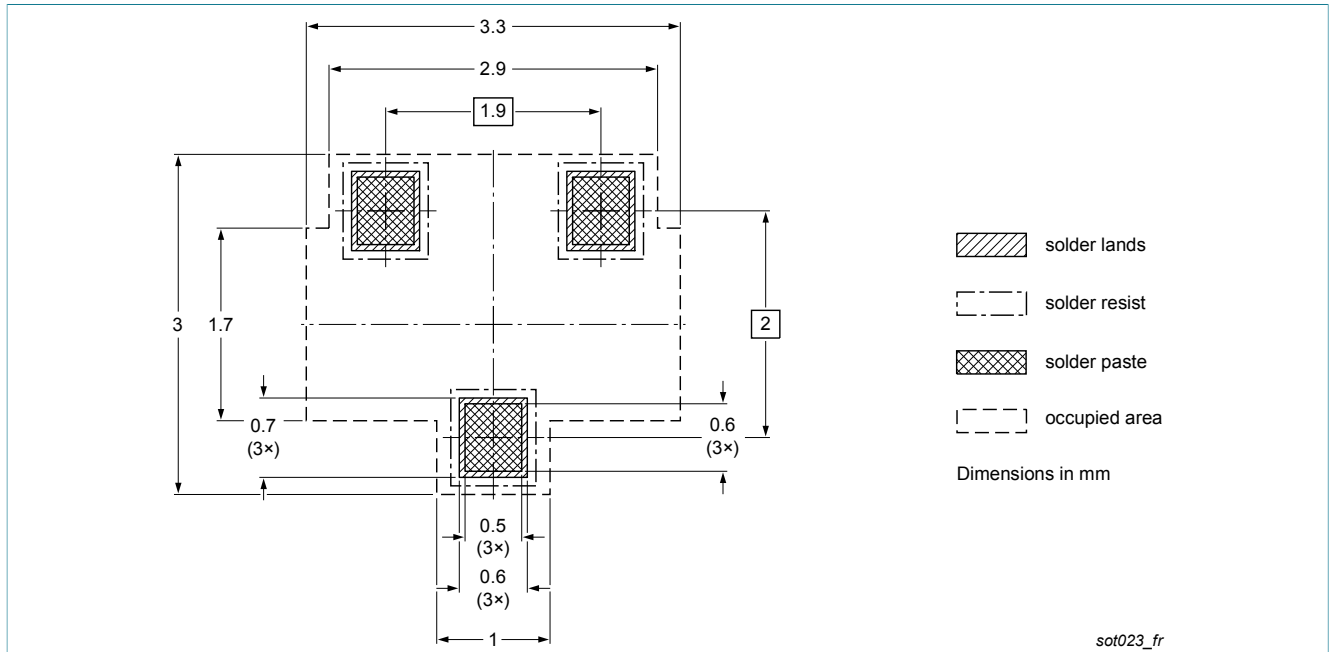


Fig. 19. Reflow soldering footprint for TO-236AB (SOT23)

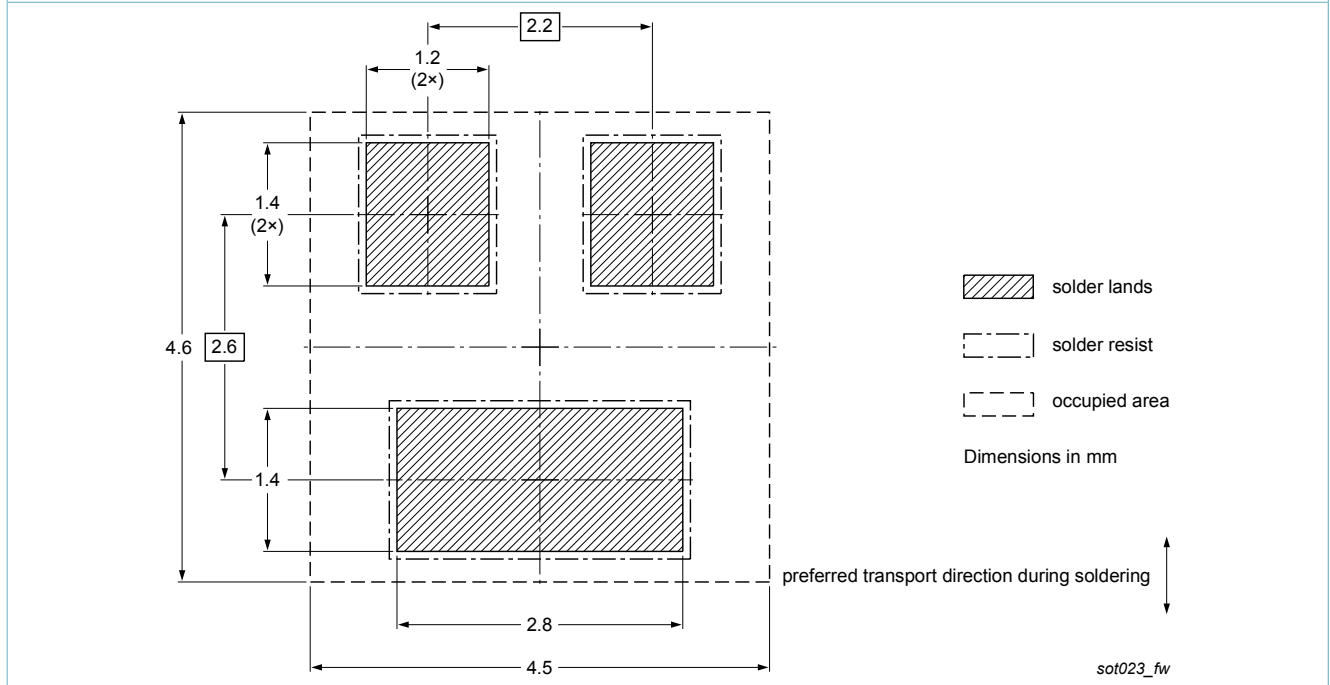


Fig. 20. Wave soldering footprint for TO-236AB (SOT23)

## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV120ENEA v.1	20160304	Product data sheet	-	-

## 15. Legal information

### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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